



Controlling topologically protected states by external fields and doping



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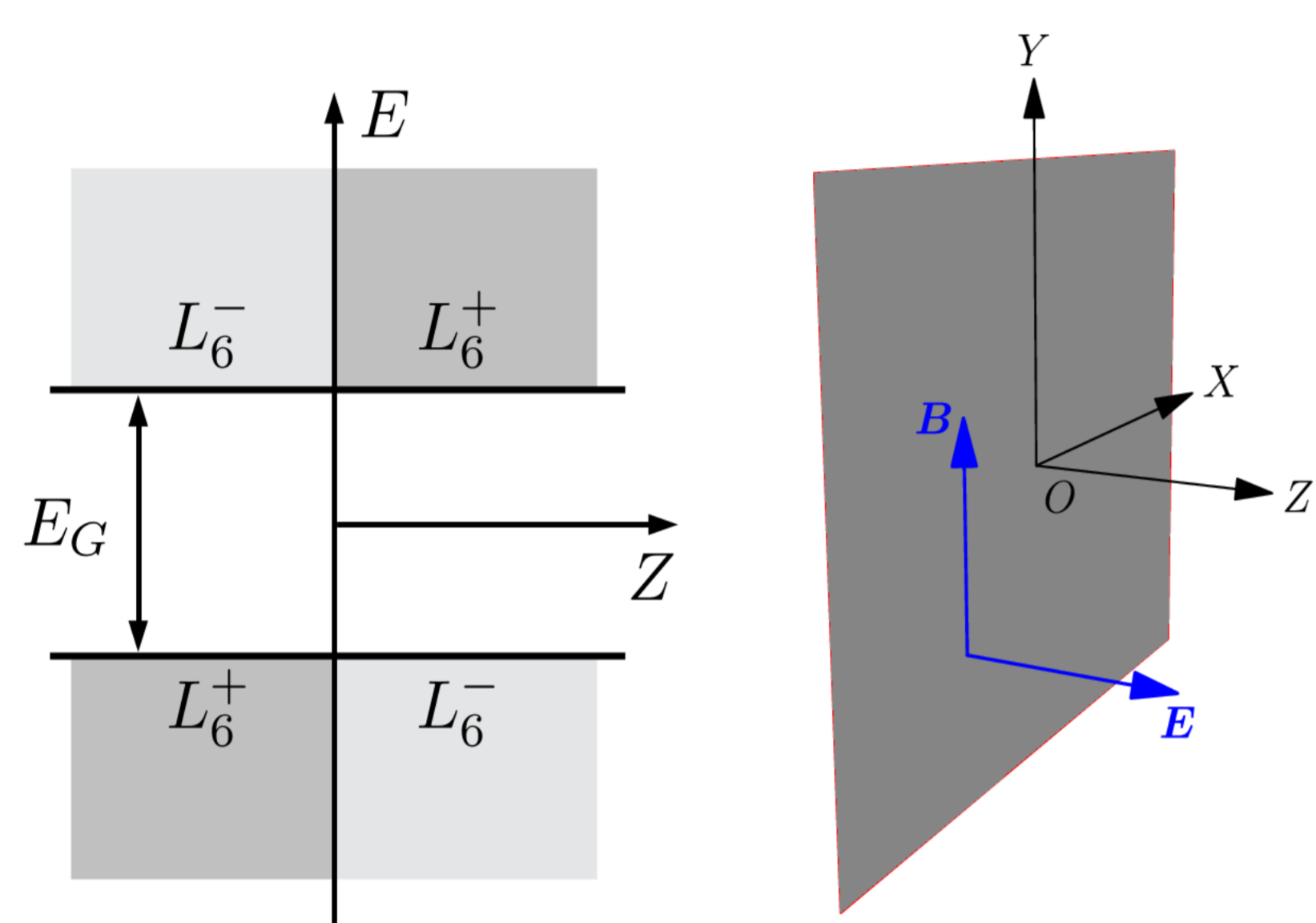
Motivation: Topologically protected surface states are foreseen to boost and reshape the current paradigm of electronics, spintronics, photonics and many other areas alike. It is therefore desirable to have a full control of their defining properties.

Systems: Three-dimensional topological insulators (e.g. Bi₂Se₃) and topological crystalline insulators (e.g. SnTe).

Main Results: External electric and magnetic fields allow to dynamically modify the Fermi velocity. δ -doping induces a coexistence between a Rashba 2DEG and the topological surface states, altering the optical transitions.

Topological Boundary

External Fields



Spinful Two-Band Model

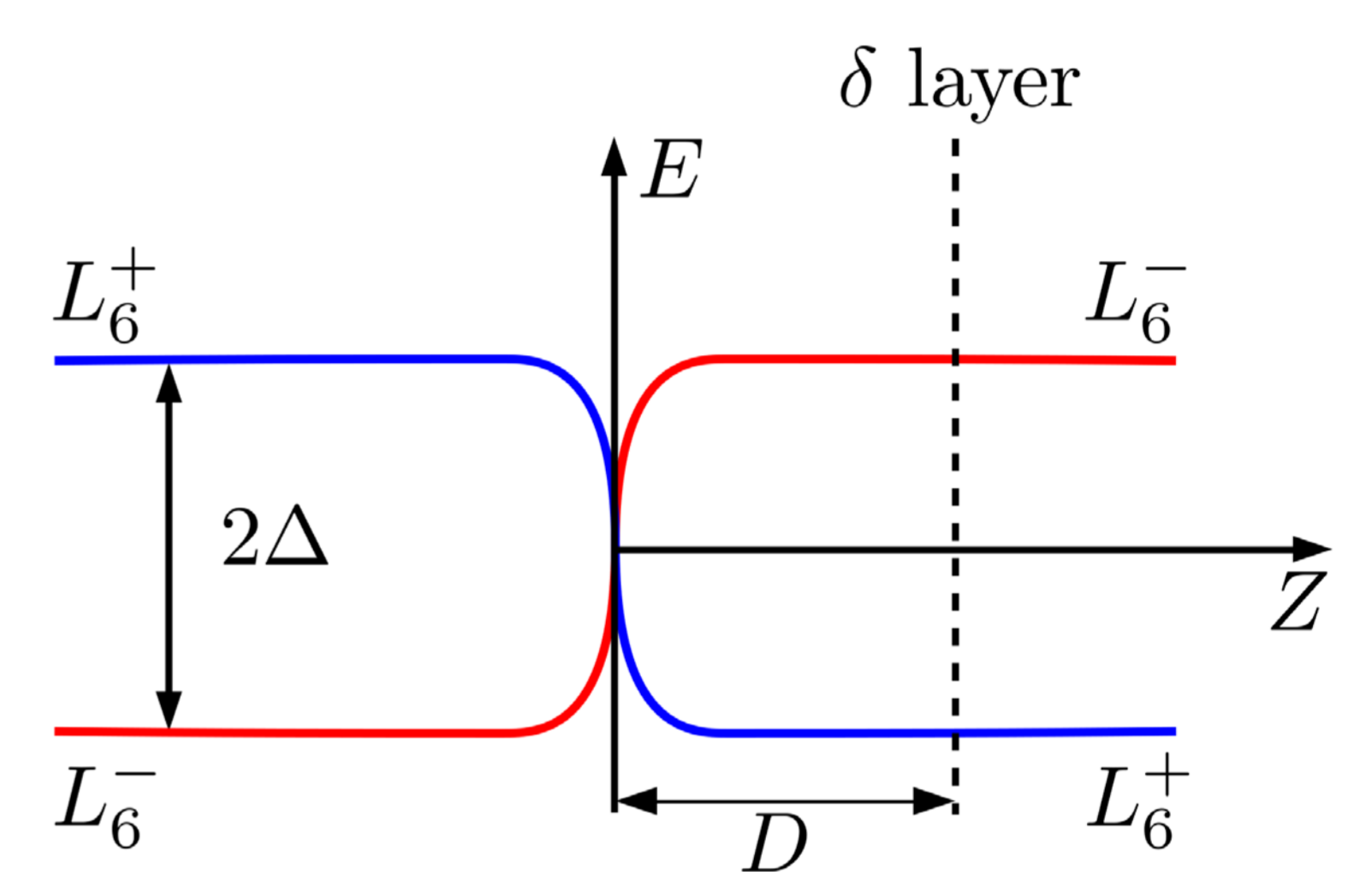
$$H = v_F \boldsymbol{\alpha} \cdot \mathbf{p} + \Delta(z)\beta + V(z)$$

$$\text{Basis: } |\psi\rangle \in \mathcal{H}_{\text{orbital}} \otimes \mathcal{H}_{\text{spin}}$$

Bulk Symmetries: \mathcal{T}, \mathcal{P}

$$\mathbb{Z}_2 \text{ topological index: } \nu = \text{sgn}(\Delta)$$

Doping



External Fields

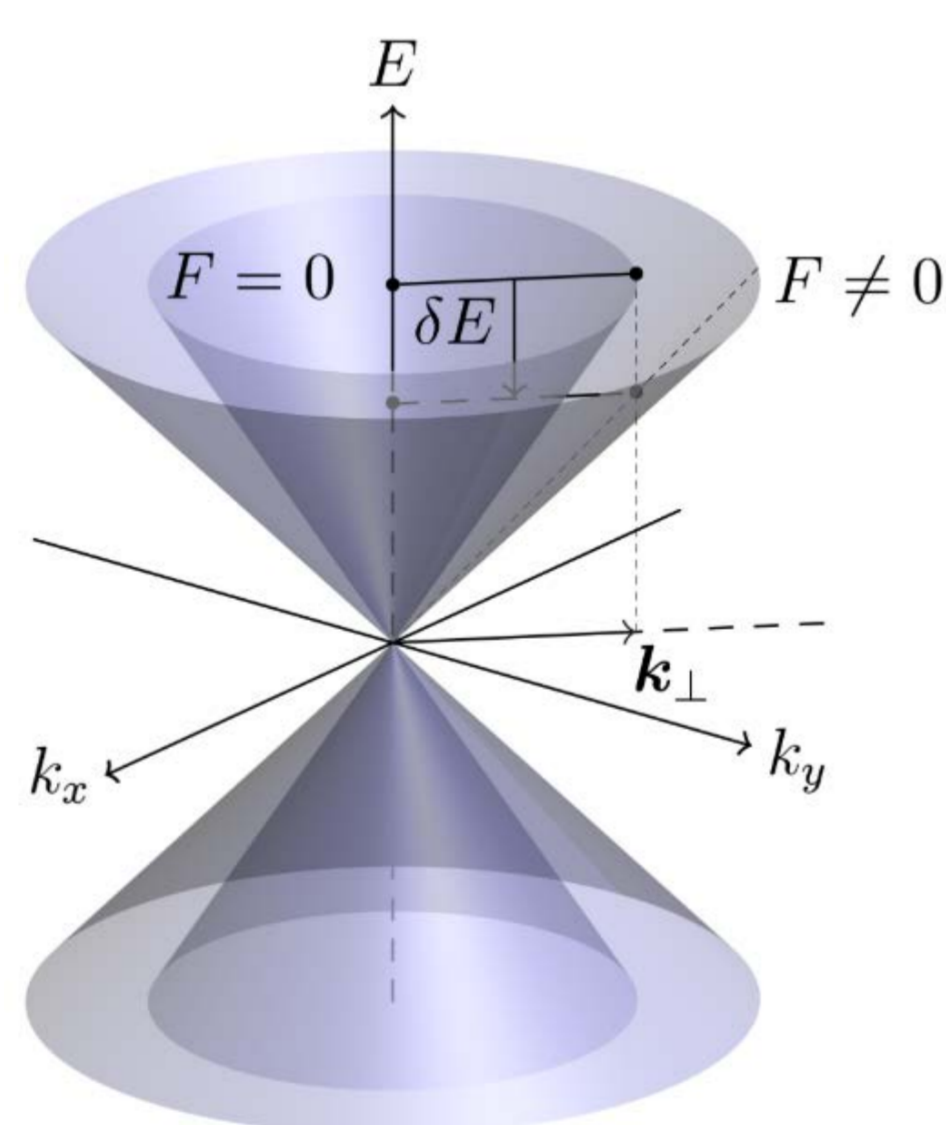
Electric Field

Isotropic Fermi velocity reduction

$$\frac{v_F(F)}{v_F(0)} = 1 - \frac{5 F^2}{8 F_C^2}$$

$$e F_C d = \Delta$$

$$d = \frac{\hbar v_F}{\Delta}$$

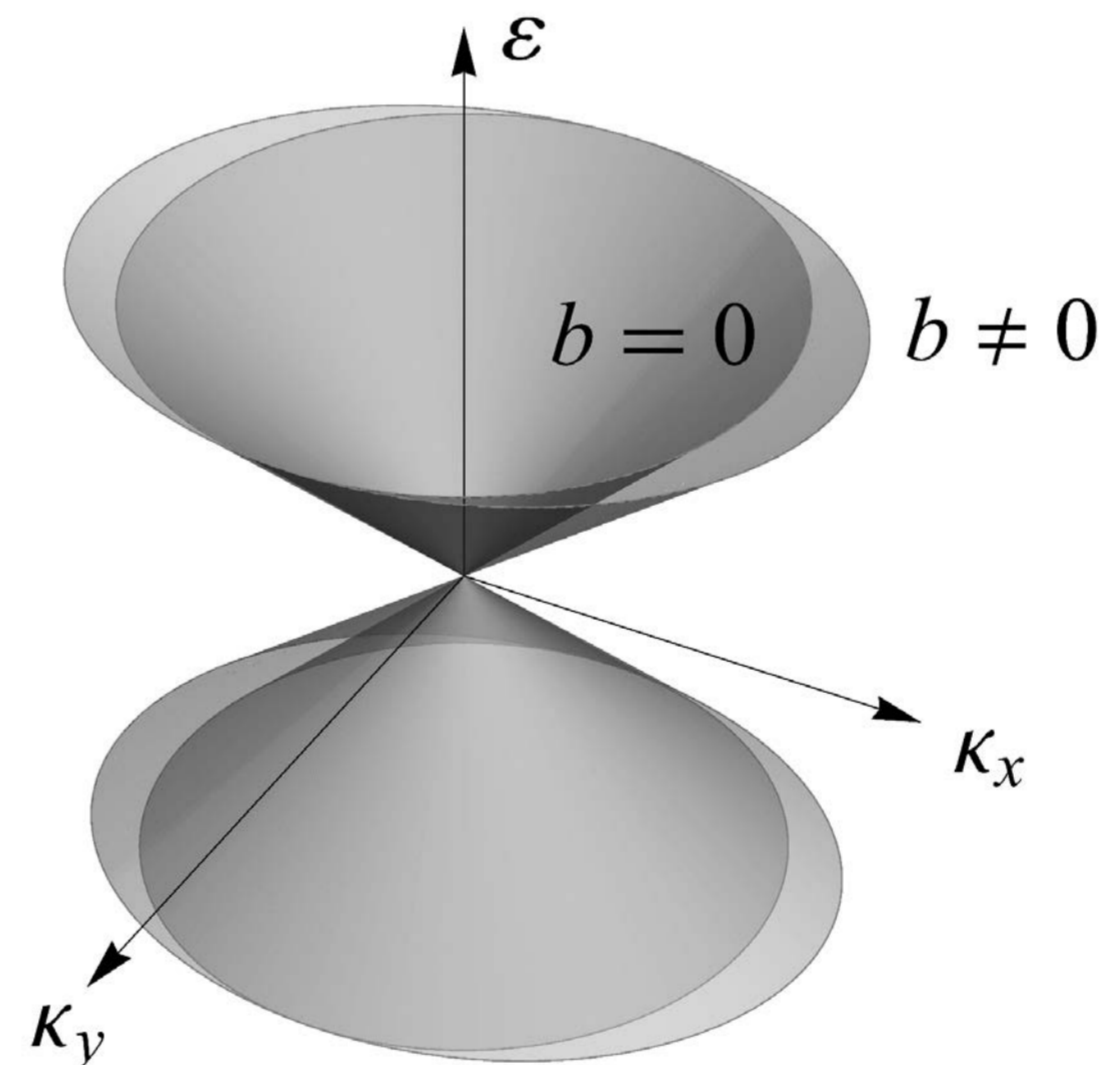


Magnetic Field

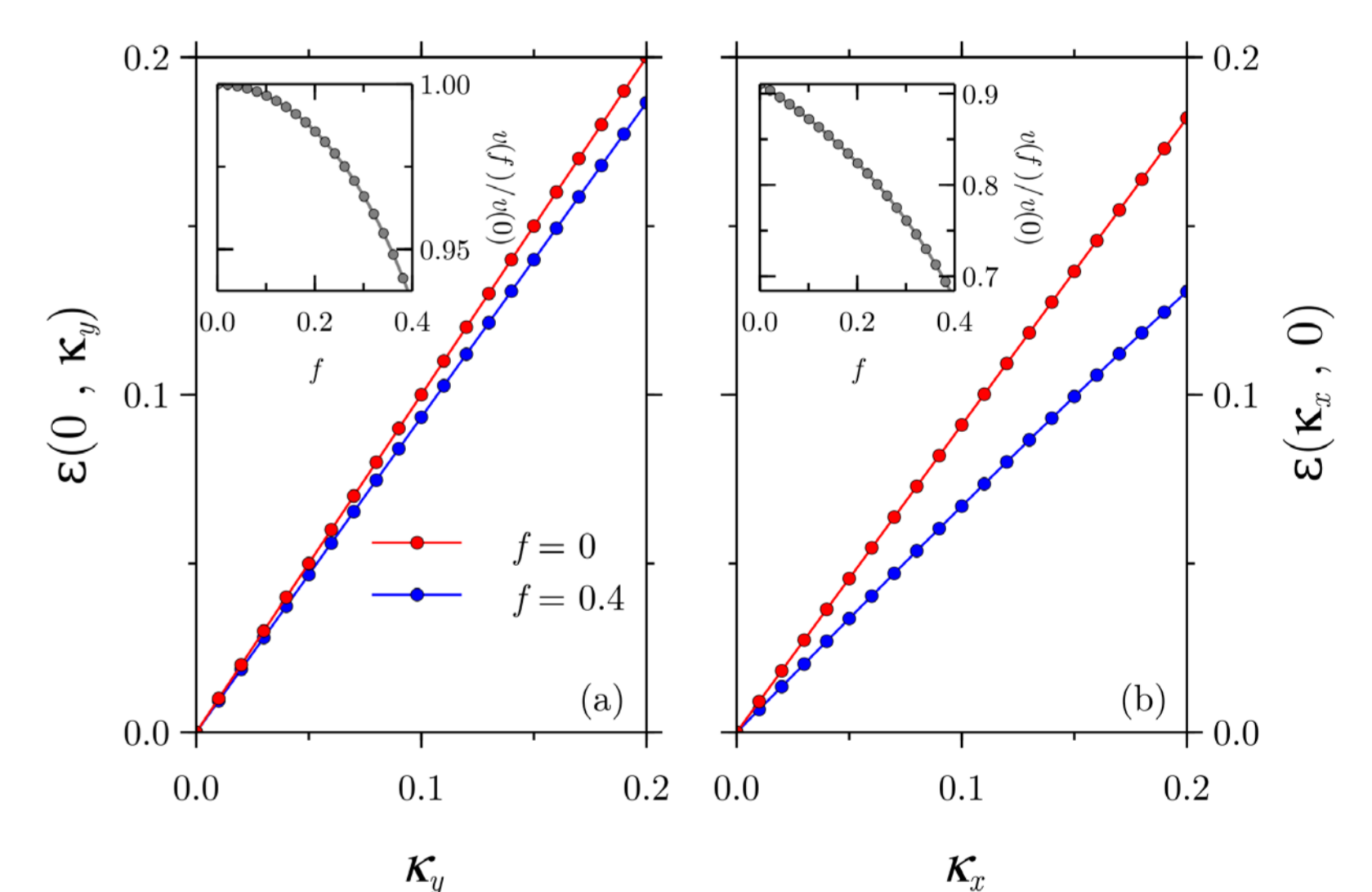
Anisotropic Fermi velocity reduction

$$\frac{v_F^x(B)}{v_F^x(0)} = 1 - \frac{5 d^2}{\ell_B^2}$$

$$\ell_B = \sqrt{\frac{\hbar}{eB}}$$

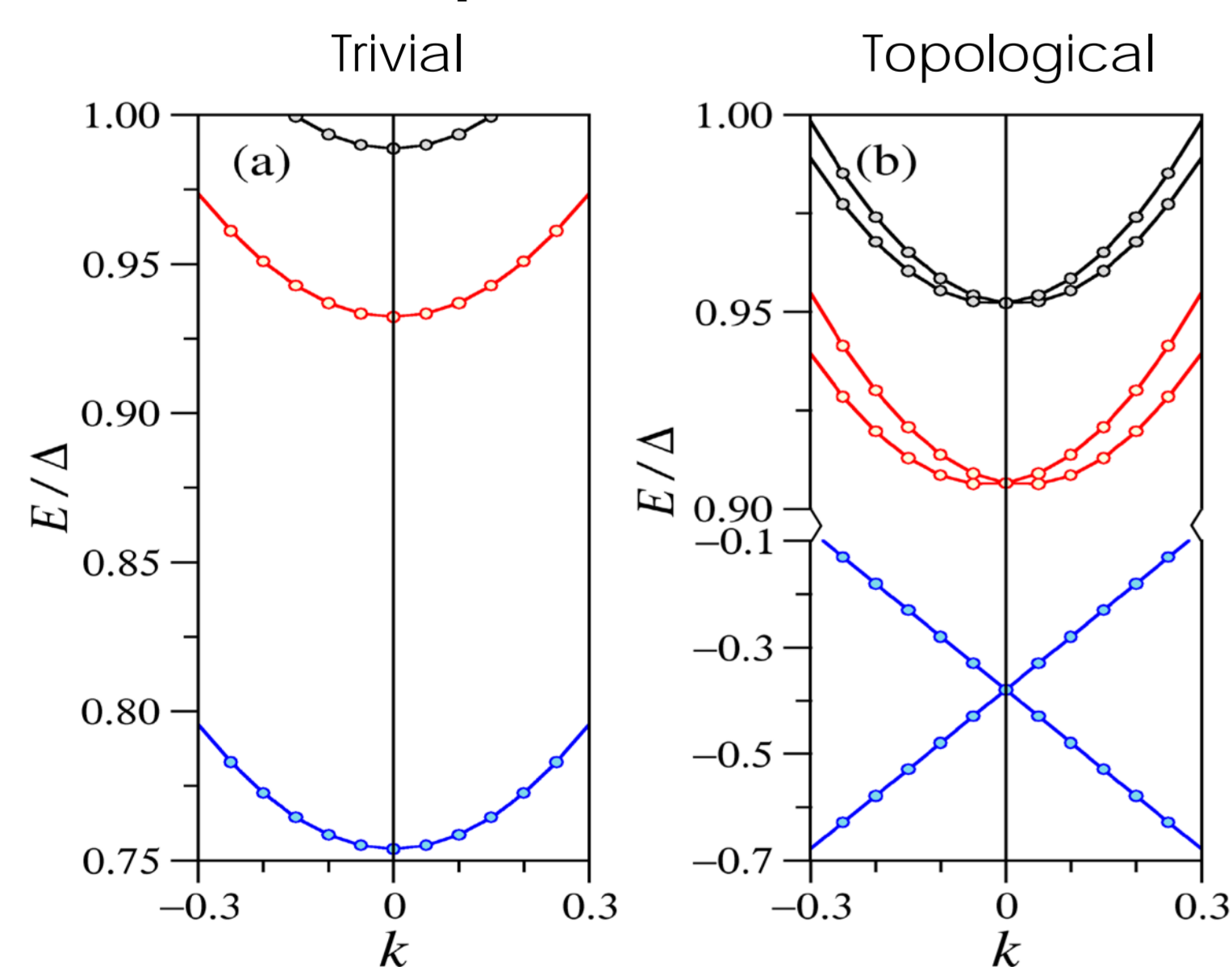


Crossed Fields

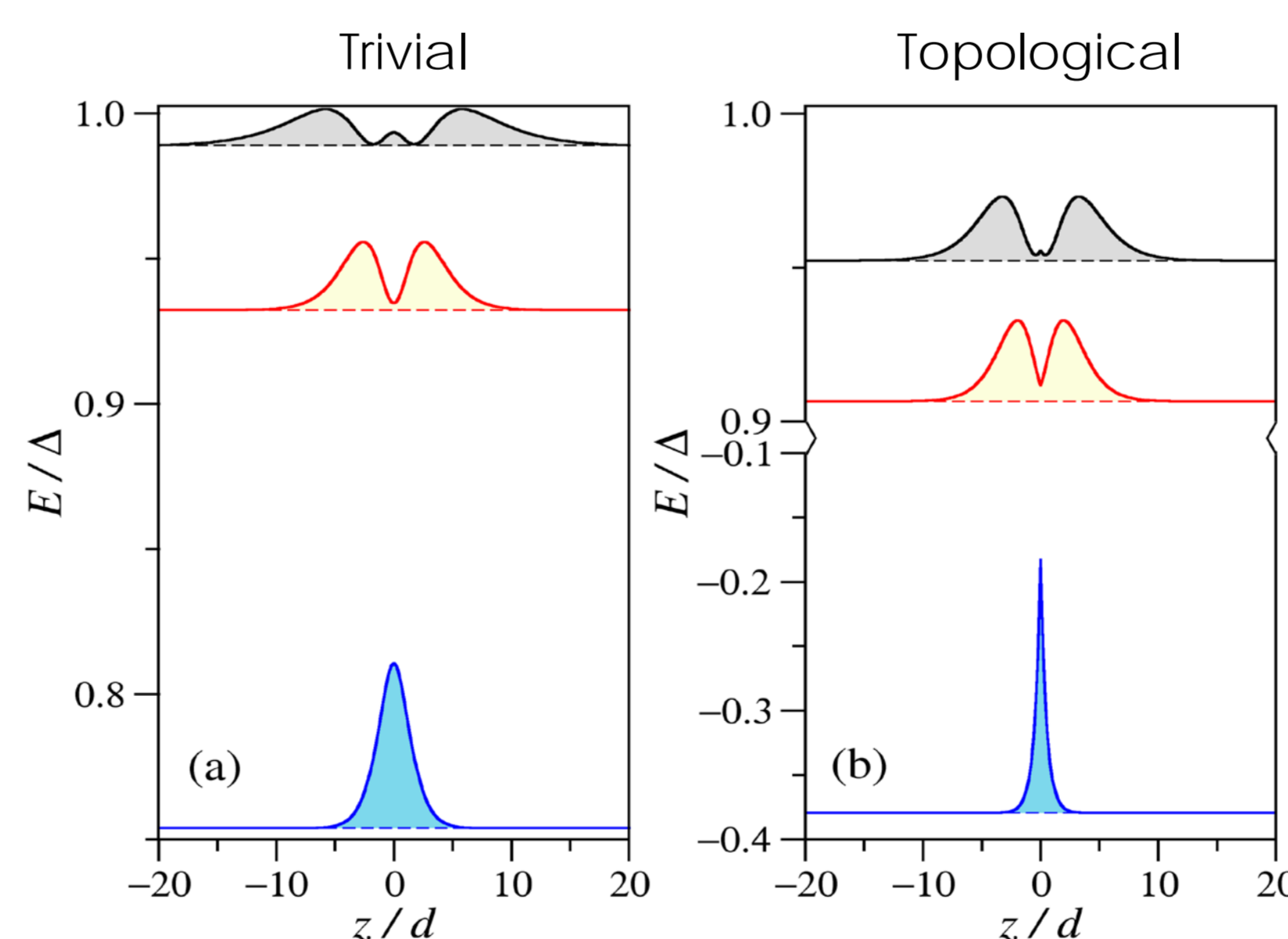


δ -doping

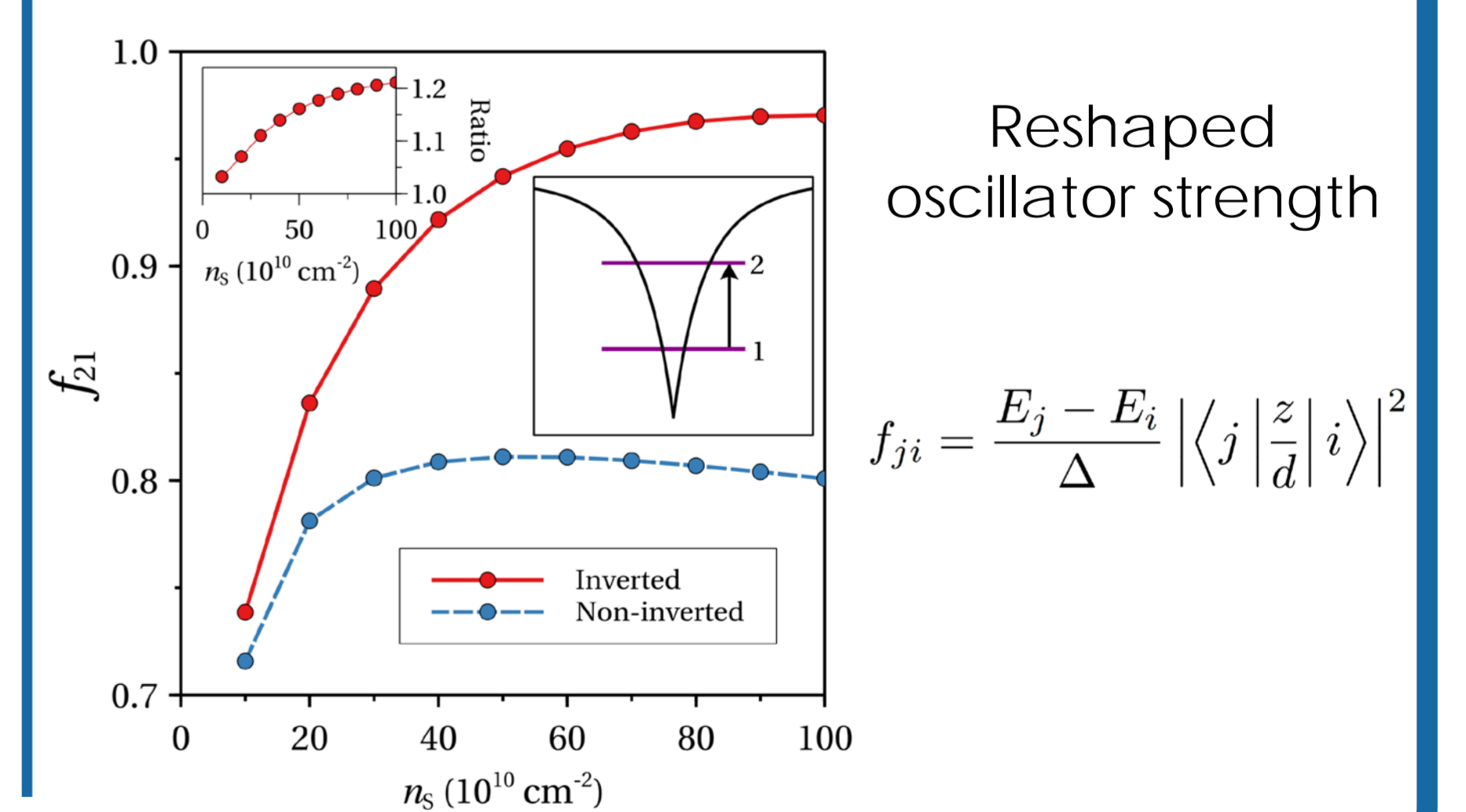
Spectrum



States



Optical Transitions



Conclusions

- Topological surface states are robust against perturbations.
- Dirac dispersion can be modified externally.
- Rashba-like 2DEG coexists with topological surface state.
- Linear optical response is reshaped by the topological state.

References

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